# MSKSEMI 美森科













**ESD** 

1/5

TSS

MOV

GDT

PLED

## MSESD16F7VPU

Product specification





#### **Features**

- 2-pin lead-less package
- Junction capacitance (Max value: 900pF)
- Peak Pulse Current (8/20µs):115A
- IEC61000-4-2 (ESD) ±30kV (air), ±30kV (contact)
- Low clamping voltage
- Low leakage current
- Working voltages:7V
- RoHS Compliant

## **Mechanical Characteristics**

- Package: DFN1610-2L
- Lead Finish:Matte Tin
- Case Material: "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020

## **Applications**

- DC port
- Notebooks and Handhelds, Audio Players, Peripherals
- Personal Digital Assistants, Portable Instrumentation
- Keypads, Side Keys, LCD Displays

#### **Reference News**

DFN1610-2L	Graphic symbol	Marking	
	O Uni-directional	7P	



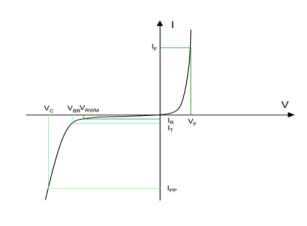
## Absolute Maximum Ratings (T=25°C, RH=45%-75%, unless otherwise noted)

Parameters	Symbol	Value	Unit
Peak Pulse Power (tp=8/20µs waveform)	РР	2300	W
Peak Pulse Current (8/20μs)	<b> </b> PP	115	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	Vesd	±30 ±30	KV
Operating Temperature Range	Tı	−55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

## Electrical Characteristics (T=25°C, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Reverse Working Voltage	VRWM				7	V
Reverse Breakdown Voltage	$V_{BR}$	l <sub>R</sub> = 1mA	7.5		10	V
Reverse Leakage Current	<b>I</b> R	V <sub>R</sub> = 7V			0.5	uA
Clamping voltage	Vc	I <sub>PP</sub> = 10A,T <sub>P</sub> =8/20us			10	V
Clamping voltage	Vc	I <sub>PP</sub> = 115A,T <sub>P</sub> =8/20us			20	V
Junction capacitance	CJ	V <sub>R</sub> =0V,f =1MHz			900	pF

Symbol	Parameter	
VRWM	Peak Reverse Working Voltage	
lR	Reverse Leakage Current @VRWM	
VBR	Breakdown Voltage @l⊤	
lτ	Test Current	
IPP	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @IPP	
Ppp	Peak Pulse Power	
Сл	Junction Capacitance	
lF	Forward Current	
VF	Forward Voltage @IF	





## **Typical Characteristics**

FIG1: Power rating derating curve

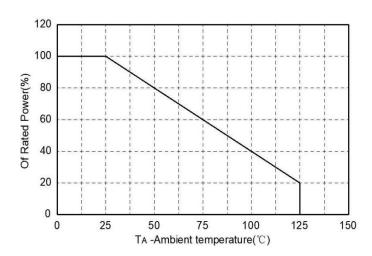


FIG2: pulse Waveform

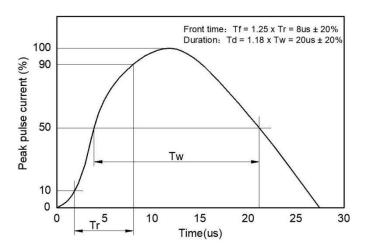


FIG3: Capacitance between terminals characteristics

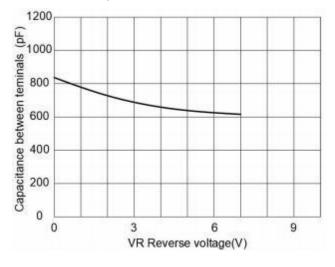
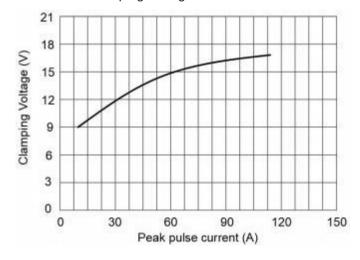


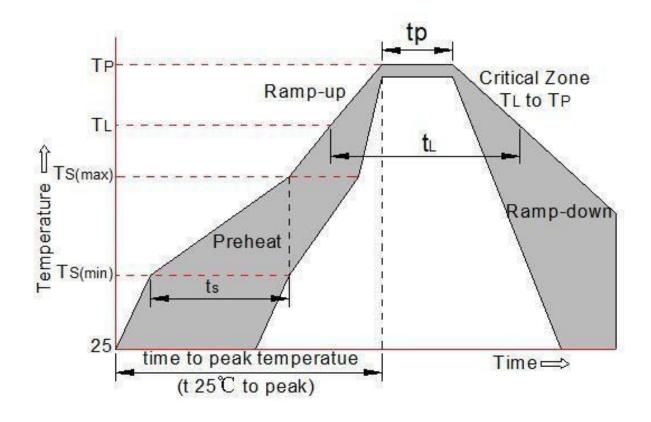
FIG4: Clamping Voltage vs. Peak Pulse Current





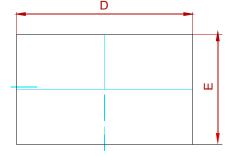
## **Soldering Parameters**

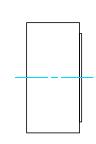
	Reflow Condition	Pb-Free assembly (see as bellow)
	-Temperature Min (T <sub>s(min)</sub> )	+150℃
Pre Heat	-Temperature Max(T <sub>s(max)</sub> )	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Averag	e ramp up rate (Liquid us Temp (Tւ) to peak)	3℃/sec. Max
	$T_{s(max)}$ to $T_L$ - Ramp-up Rate	3℃/sec. Max
D-9	-Temperature(T <sub>∟</sub> ) (Liquid us)	+217℃
Reflow	-Temperature(t₋)	60-150 secs.
	Peak Temp (T <sub>p</sub> )	+260(+0/-5)°C
	Time within 5℃of actual Peak Temp (t٫)	30 secs. Max
	Ramp-down Rate	6℃/sec. Max
	Time 25℃to Peak Temp (T <sub>P</sub> )	8 min. Max
	Do not exceed	+260℃

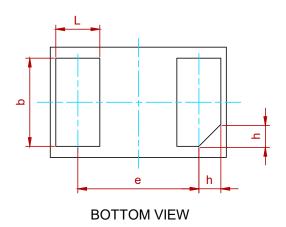




## PACKAGE MECHANICAL DATA







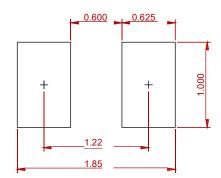
**TOP VIEW** 



SIDE VIEW

O. m. h. a.l.	Dimensions in Millimeters		
Symbol	Min.	Тур.	Max.
A	0.45	0.50	0.60
A1	0.00	0.02	0.05
С	0.15 Ref.		
b	0.75	0.80	0.95
L	0.35	0.40	0.45
D	1.55	1.60	1.70
E	0.95	1.00	1.10
е	1.10 BSC		
h	0.20 Ref.		

#### Recommend PCB Layout (Unit: mm)



#### Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
MSESD16F7VPU	DFN1610-2L	3000



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